



Substitute for form 1449A/B/PTO			Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Application Number	10/716,455-Conf. #6664
			Filing Date	November 20, 2003
			First Named Inventor	Takashi Takahashi
			Art Unit	2811
			Examiner Name	Not Yet Assigned
			Attorney Docket Number	R2184.0271/P271
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Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Kang, Donghee

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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PTO/SB/08a/b (08-03)

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